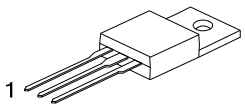
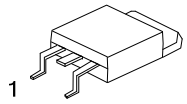
UTT25P10

Preliminary | ***Power MOSFET***

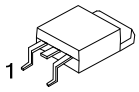
25A, 100V P-CHANNEL POWER MOSFET



TO-220



TO-263



TO-252

■ DESCRIPTION

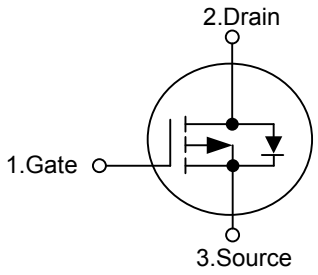
The UTC **UTT25P10** is a P-channel power MOSFET using UTC's advanced technology to provide the customers with high switching speed and a minimum on-state resistance, and it can also withstand high energy in the avalanche.

This UTC **UTT25P10** is suitable for motor drivers, switching regulators, converters and relay drivers, etc.

■ FEATURES

* $R_{DS(ON)}$<0.15Ω @ V_{GS}=-10V, I_D= -25A
* High Switching Speed

■ SYMBOL



■ ORDERING INFORMATION

Ordering Number		Package	Pin Assignment			Packing
Lead Free	Halogen Free		1	2	3	
UTT25P10L-TA3-T	UTT25P10G-TA3-T	TO-220	G	D	S	Tube
UTT25P10L-TN3-T	UTT25P10G-TN3-T	TO-252	G	D	S	Tube
UTT25P10L-TN3-R	UTT25P10G-TN3-R	TO-252	G	D	S	Tape Reel
UTT25P10L-TQ2-T	UTT25P10G-TQ2-T	TO-263	G	D	S	Tube
UTT25P10L-TQ2-R	UTT25P10G-TQ2-R	TO-263	G	D	S	Tape Reel

Note: Pin Assignment: G: Gate D: Drain S: Source

UTT25P10L-TA3-T (1)Packing Type (2)Package Type (3)Lead Free	(1) T: Tube, R: Tape Reel (2) TA3: TO-220, TN3: TO-252, TQ2: TO-263 (3) L: Lead Free, G: Halogen Free

■ ABSOLUTE MAXIMUM RATINGS (T_C=25°C, unless otherwise specified)

PARAMETER		SYMBOL	RATINGS	UNIT
Drain-Source Voltage (Note 2)		V_{DSS}	-100	V
Drain-Gate Voltage (R_{GS}=20kΩ)		V_{DGR}	-100	V
Gate-Source Voltage		V_{GSS}	±20	V
Drain Current	Continuous	I_D	-25	A
	Pulsed (Note 2)	I_{DM}	-60	A
Power Dissipation	TO-220/TO-263	P_D	100	W
	TO-252		50	
Junction Temperature		T_J	-55~+150	°C
Storage Temperature		T_{STG}	-55~+150	°C

Notes: 1. Absolute maximum ratings are those values beyond which the device could be permanently damaged. Absolute maximum ratings are stress ratings only and functional device operation is not implied.
2. Repetitive rating: pulse width limited by maximum junction temperature.

■ THERMAL CHARACTERISTICS

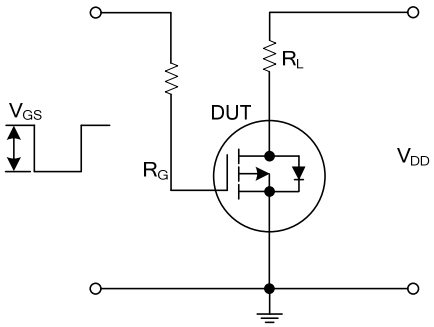
PARAMETER		SYMBOL	RATINGS	UNIT
Junction to Case	TO-220/TO-263	θ_{JC}	0.83	°C/W
	TO-252		2.5	

■ ELECTRICAL CHARACTERISTICS (T_C=25°C, unless otherwise specified)

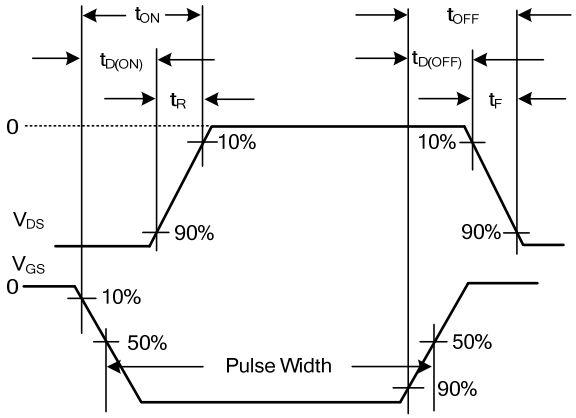
PARAMETER		SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
OFF CHARACTERISTICS							
Drain-Source Breakdown Voltage		BV_{DSS}	I_D= -250μA, V_{GS}=0V	-100			V
Drain-Source Leakage Current		I_{DSS}	V_{DS}=Rated BV_{DSS}, V_{GS}=0V			-1	μA
			V_{DS}=0.8xRated BV_{DSS}, V_{GS}=0V , T_C=125°C			-25	
Gate- Source Leakage Current	Forward	I_{GSS}	V_{GS}=+20V, V_{DS}=0V			+100	nA
	Reverse		V_{GS}=-20V, V_{DS}=0V			-100	nA
ON CHARACTERISTICS							
Gate Threshold Voltage		$V_{GS(TH)}$	V_{DS}=V_{GS}, I_D= -250μA	-2		-4	V
Static Drain-Source On-State Resistance		$R_{DS(ON)}$	V_{GS}=-10V, I_D= -25A			0.15	Ω
DYNAMIC PARAMETERS							
Input Capacitance		C_{ISS}	V_{GS}=0V, V_{DS}=-25V, f=1MHz			3000	pF
Output Capacitance		C_{OSS}				1500	pF
Reverse Transfer Capacitance		C_{RSS}				600	pF
SWITCHING PARAMETERS							
Turn-ON Delay Time		$t_{D(ON)}$	I_D≈ -12.5A, V_{DS}=-50V, R_{GS}=50Ω,V_{GS}=-10V, R_L=4.0Ω		35	100	ns
Rise Time		t_R			165	250	ns
Turn-OFF Delay Time		$t_{D(OFF)}$			270	800	ns
Fall-Time		t_F			165	250	ns
SOURCE- DRAIN DIODE RATINGS AND CHARACTERISTICS							
Drain-Source Diode Forward Voltage (Note 1)		V_{SD}	I_{SD}=-12.5A,			-1.4	V

Note: Pulse test: pulse width ≤ 300μs, duty cycle ≤ 2%.

■ TEST CIRCUITS AND WAVEFORMS



Switching Time Test Circuit



Resistive Switching Waveforms